Power LDMOS transistor

AMPLEON

Rev. 2 — 24 May 2017

Product data sheet

1. Product profile

1.1 General description

160 W LDMOS power transistor for base station applications at frequencies from 2110 MHz to 2200 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 ℃ in a common source class-AB demo application.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	G _p	η_D	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2110 to 2170	864	28	35	18.4	33	-31 ^[1]

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.

1.2 Features and benefits

- Excellent ruggedness
- Excellent video-bandwidth enabling full band operation
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifier for W-CDMA base stations and multi carrier applications in the 2110 MHz to 2200 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		
2	gate	1 1 5	1, 4, 5
3	source [1]		, <u> </u>
4	video decoupling		3
5	video decoupling		aaa-003884
6	n.c.	6 2 7	
7	n.c.		

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	je			
	Name	Description Version			
BLC9G22LS-160VT	-	Air cavity plastic earless flanged package; 6 leads	SOT1271-2		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T_{case} = 80 °C; P_{L} = 35 W	0.47	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.44 \text{ mA}$	65.0	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 144 mA	1.55	1.9	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 700 mA	-	2.1	-	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	28	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-280	-	+280	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7200 mA	-	10.8	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5040 \text{ mA}$	-	98	-	mΩ

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1 with 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF; f_1 = 2112.5 MHz; f_2 = 2117.5 MHz; f_3 = 2162.5 MHz; f_4 = 2167.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 864 mA; T_{case} = 25 °C; unless otherwise specified; in a water cooled class-AB test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 35 W	17.3	18.4	-	dB
η_{D}	drain efficiency	P _{L(AV)} = 35 W	31	33	-	%
RLin	input return loss	P _{L(AV)} = 35 W	-	-16.1	-10	dB
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 35 W	-	-31	-27	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLC9G22LS-160VT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 864 mA; 2-carrier W-CDMA signal; P_L = 70 W (average); f_c = 2110 MHz; 5 MHz spacing; 46 % clipping.

7.2 Impedance information

Typical impedance Table 8.

Measured load-pull data of the device; I_{Dq} = 864 mA; V_{DS} = 28 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]	
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)	
Maximum	Maximum power load					
2110	2.0 - j5.6	1.4 – j3.1	199.6	58.9	15.5	
2140	2.3 – j5.9	1.3 – j3.0	198.0	58.3	15.5	
2170	2.7 – j6.4	1.3 – j3.1	197.9	58.9	15.6	
Maximum	drain efficiency lo	ad			,	
2110	2.0 - j5.6	2.6 - j1.9	135.6	67.5	17.9	
2140	2.3 – j5.9	2.3 – j1.9	139.4	67.2	17.8	
2170	2.7 – j6.4	2.3 – j1.8	132.5	67.4	18.1	

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.

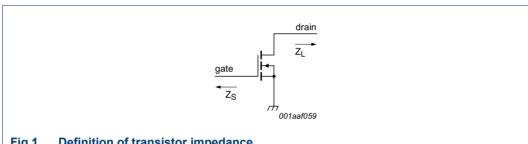


Fig 1. **Definition of transistor impedance**

7.3 Test circuit

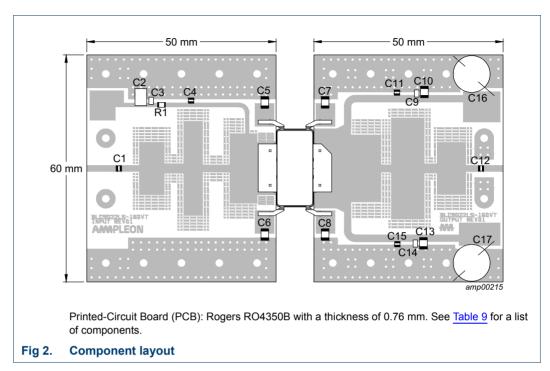


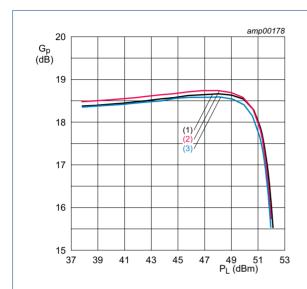
Table 9. List of components

See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C4, C11, C12, C15	multilayer ceramic chip capacitor	33 pF	ATC 800B, vertical mounting
C2	multilayer ceramic chip capacitor	1 μF	Murata: GRM32RR71H105KA01L
C3	multilayer ceramic chip capacitor	100 nF	Murata: GRM21BR71H104KA01L
C9, C14	multilayer ceramic chip capacitor	220 nF, 50 V	Murata: GRM21BR71H224KA01L
C5, C6, C7, C8, C10, C13	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata: GRM32ER71H475KA88L
C16, C17	electrolytic capacitor	> 470 μF, 50 V	low ESR
R1	chip resistor	4.7 Ω, 1 %	SMD 0805

7.4 Graphical data

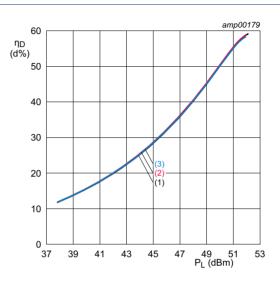
7.4.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 864 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

Fig 3. Power gain as a function of output power; typical values

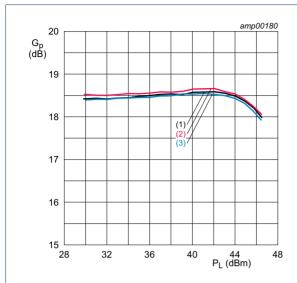


 V_{DS} = 28 V; I_{Dq} = 864 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

Fig 4. Drain efficiency as a function of output power; typical values

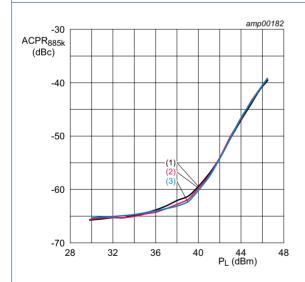
7.4.2 IS-95



 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

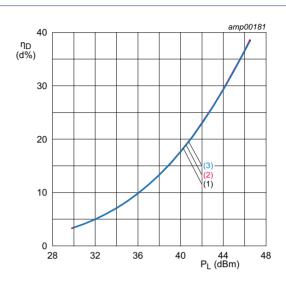
Fig 5. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 864 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

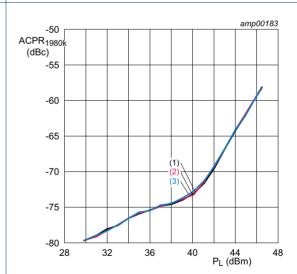
Fig 7. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 6. Drain efficiency as a function of output power; typical values

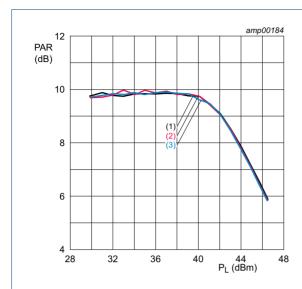


 $V_{DS} = 28 \text{ V}; I_{Da} = 864 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 8. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

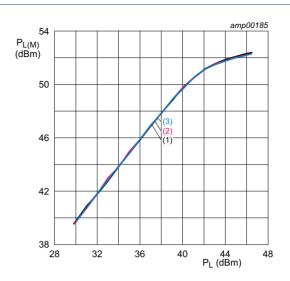
Power LDMOS transistor



 $V_{DS} = 28 \text{ V}; I_{Dq} = 864 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 9. Peak-to-average power ratio as a function of output power; typical values

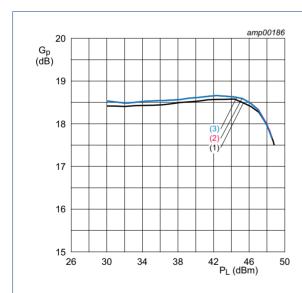


 $V_{DS} = 28 \text{ V}; I_{Dq} = 864 \text{ mA}.$

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 10. Peak output power as a function of output power; typical values

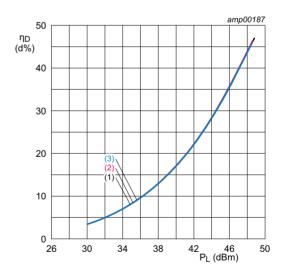
7.4.3 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2112.5 MHz
- (2) f = 2140 MHz
- (3) f = 2167.5 MHz

Fig 11. Power gain as a function of output power; typical values

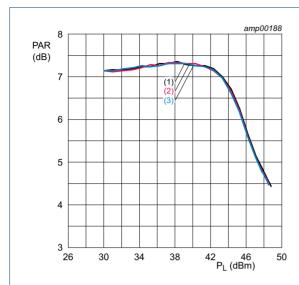


 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2112.5 MHz
- (2) f = 2140 MHz
- (3) f = 2167.5 MHz

Fig 12. Drain efficiency as a function of output power; typical values

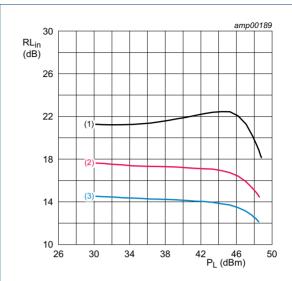
Power LDMOS transistor



 $V_{DS} = 28 \text{ V}; I_{Dq} = 864 \text{ mA}.$

- (1) f = 2112.5 MHz
- (2) f = 2140 MHz
- (3) f = 2167.5 MHz

Fig 13. Peak-to-average power ratio as a function of output power; typical values

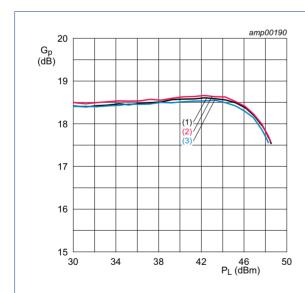


 $V_{DS} = 28 \text{ V}; I_{Da} = 864 \text{ mA}.$

- (1) f = 2112.5 MHz
- (2) f = 2140 MHz
- (3) f = 2167.5 MHz

Fig 14. Input return loss as a function of output power; typical values

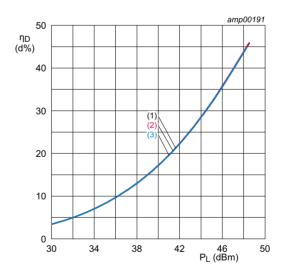
7.4.4 2-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

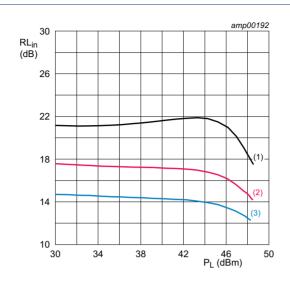
Fig 15. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

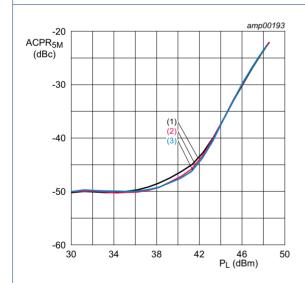
Fig 16. Drain efficiency as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

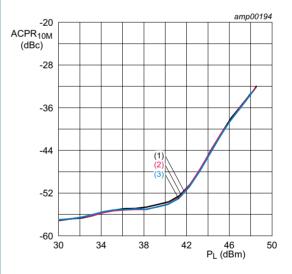
Fig 17. Input return loss as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 18. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

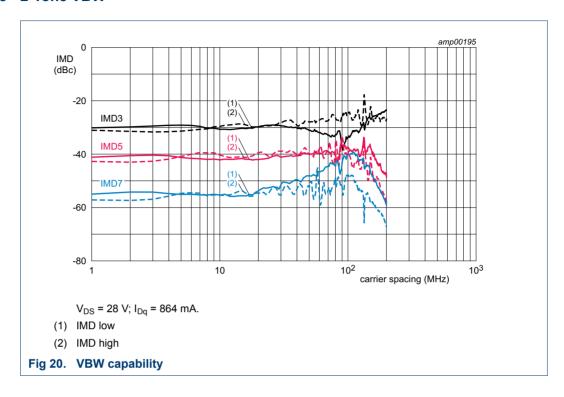


 V_{DS} = 28 V; I_{Dq} = 864 mA.

- (1) f = 2115 MHz
- (2) f = 2140 MHz
- (3) f = 2165 MHz

Fig 19. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

7.4.5 2-Tone VBW



8. Package outline

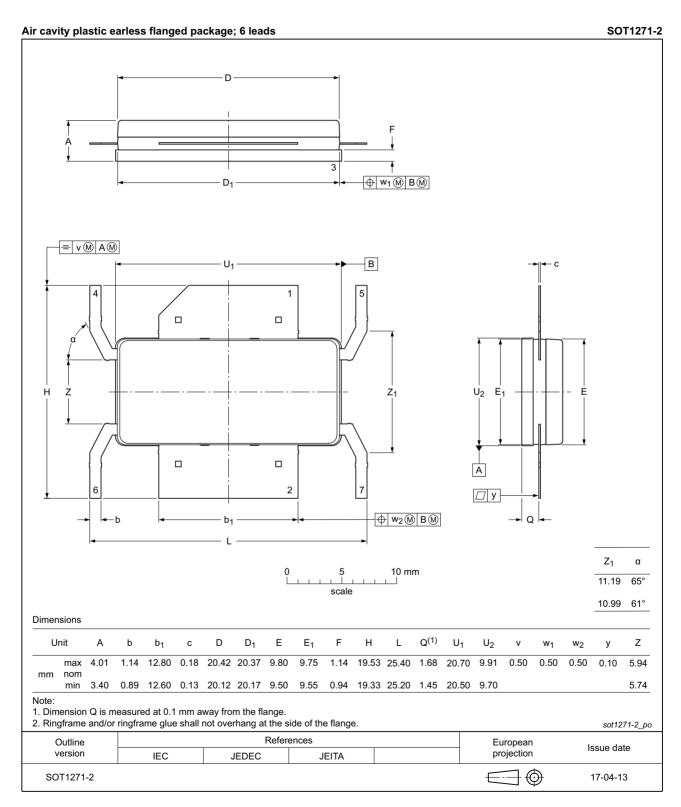


Fig 21. Package outline SOT1271-2

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 10. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

^[1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

10. Abbreviations

Table 11. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
ESR	Equivalent Series Resistance
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLC9G22LS-160VT v.2	20170524	Product data sheet		BLC9G22LS-160VT v.1	
Modifications:	<u>Table 3 on page 2</u> : change version to SOT1271-2				
	 Figure 21 on page 12: change package outline drawing to SOT1271-2 				
BLC9G22LS-160VT v.1	20170104	Product data sheet	-	-	

BLC9G22LS-160VT

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^[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

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12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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